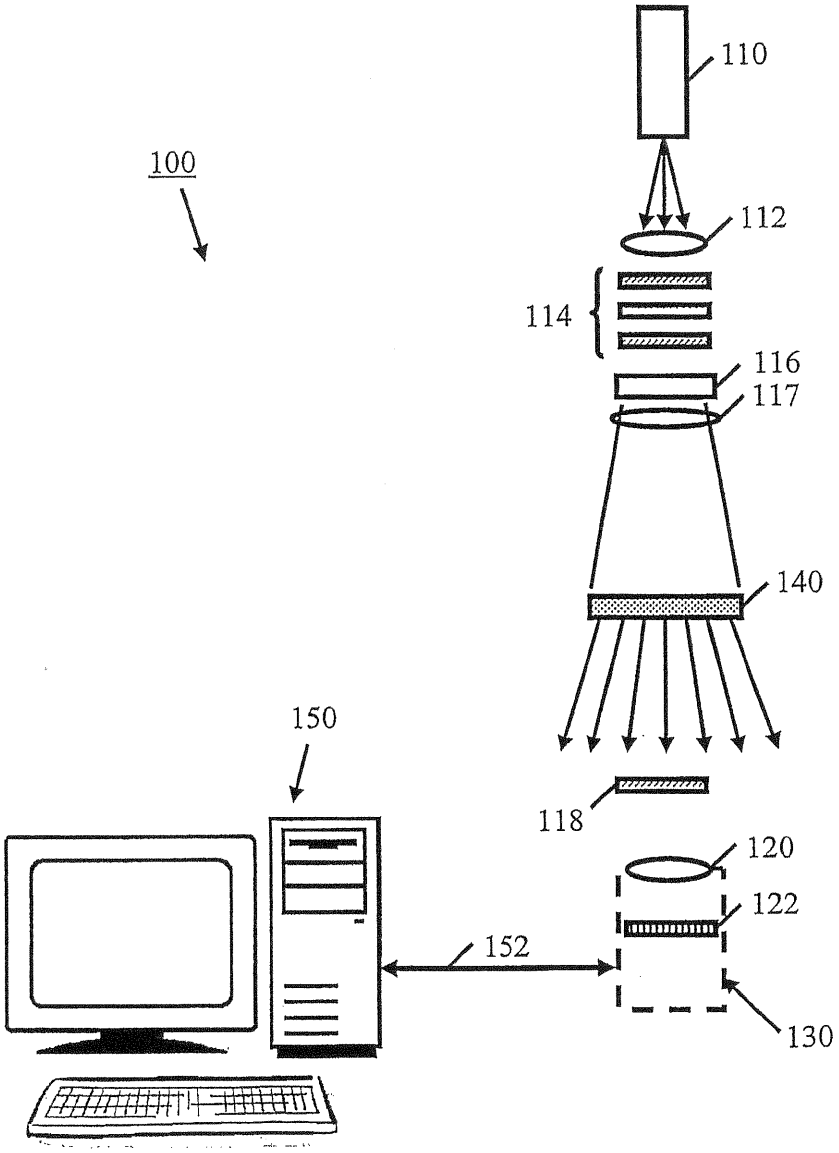


FIG. 1

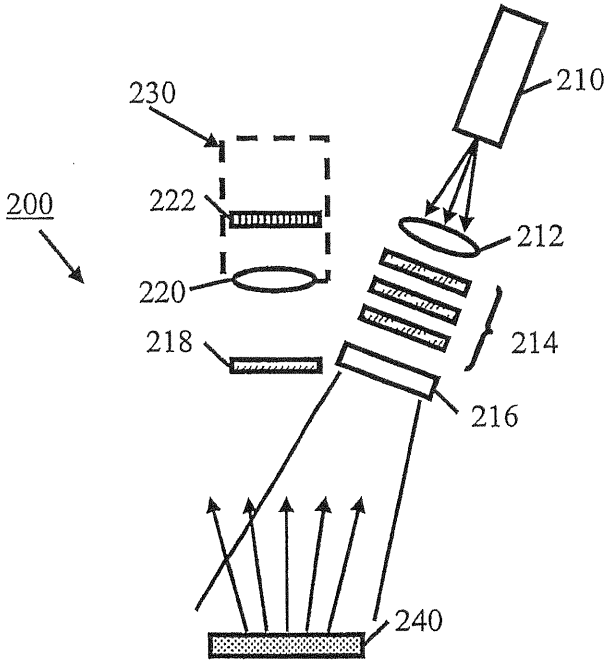

230
210
200
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FIG. 2

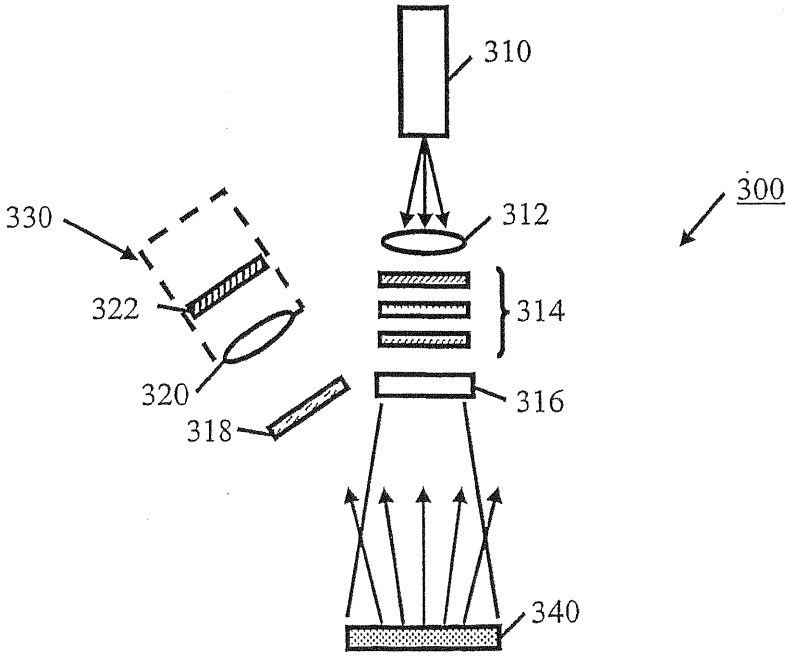

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FIG. 3

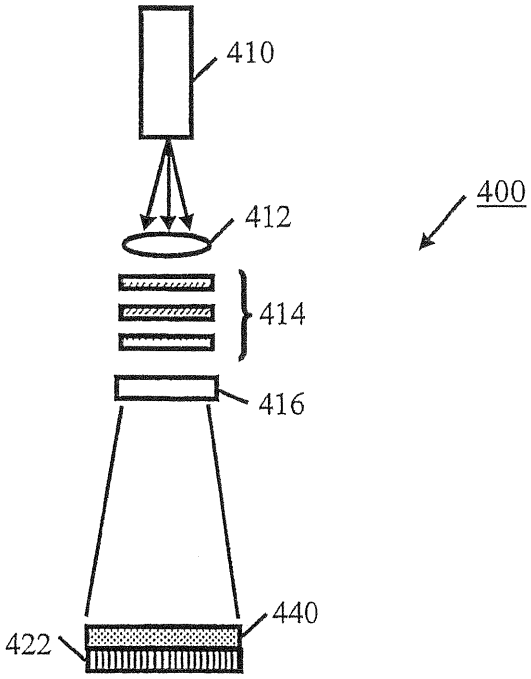


FIG. 4

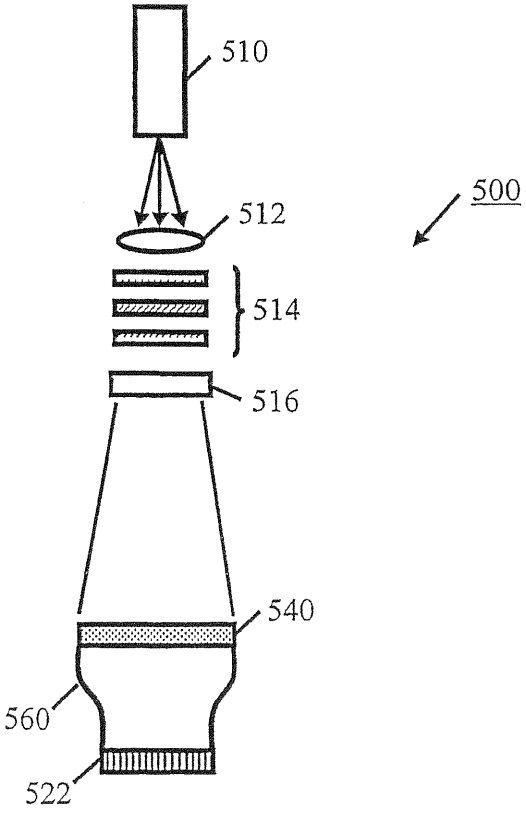


FIG. 5

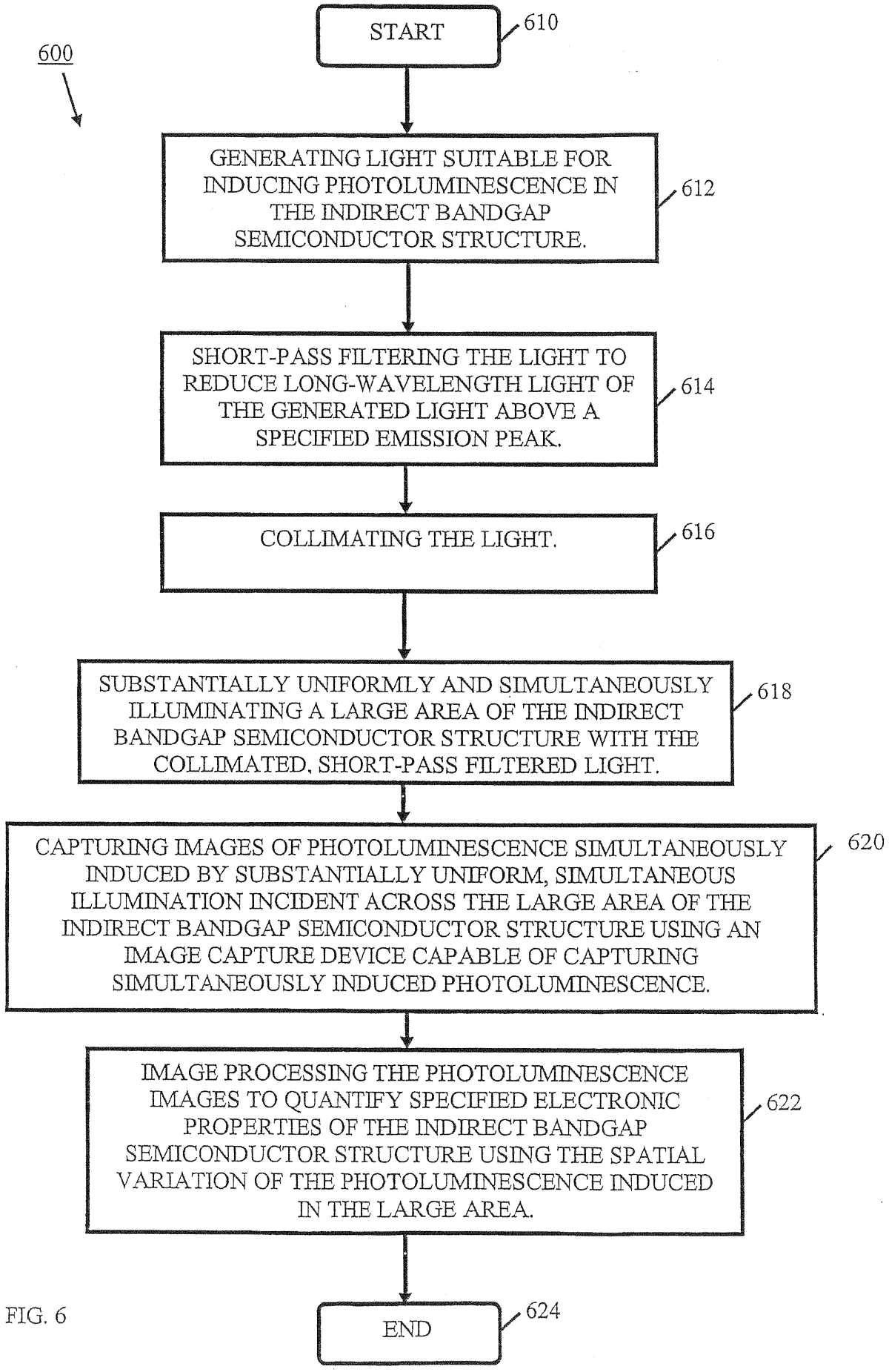

600
START
610
GENERATING LIGHT SUITABLE FOR INDUCING PHOTOLUMINESCENCE IN THE INDIRECT BANDGAP SEMICONDUCTOR STRUCTURE.
612
SHORT-PASS FILTERING THE LIGHT TO REDUCE LONG-WAVELENGTH LIGHT OF THE GENERATED LIGHT ABOVE A SPECIFIED EMISSION PEAK.
614
COLLIMATING THE LIGHT.
616
SUBSTANTIALLY UNIFORMLY AND SIMULTANEOUSLY ILLUMINATING A LARGE AREA OF THE INDIRECT BANDGAP SEMICONDUCTOR STRUCTURE WITH THE COLLIMATED, SHORT-PASS FILTERED LIGHT.
618
CAPTURING IMAGES OF PHOTOLUMINESCENCE SIMULTANEOUSLY INDUCED BY SUBSTANTIALLY UNIFORM, SIMULTANEOUS ILLUMINATION INCIDENT ACROSS THE LARGE AREA OF THE INDIRECT BANDGAP SEMICONDUCTOR STRUCTURE USING AN IMAGE CAPTURE DEVICE CAPABLE OF CAPTURING SIMULTANEOUSLY INDUCED PHOTOLUMINESCENCE.
620
IMAGE PROCESSING THE PHOTOLUMINESCENCE IMAGES TO QUANTIFY SPECIFIED ELECTRONIC PROPERTIES OF THE INDIRECT BANDGAP SEMICONDUCTOR STRUCTURE USING THE SPATIAL VARIATION OF THE PHOTOLUMINESCENCE INDUCED IN THE LARGE AREA.
622
END
624

FIG. 6

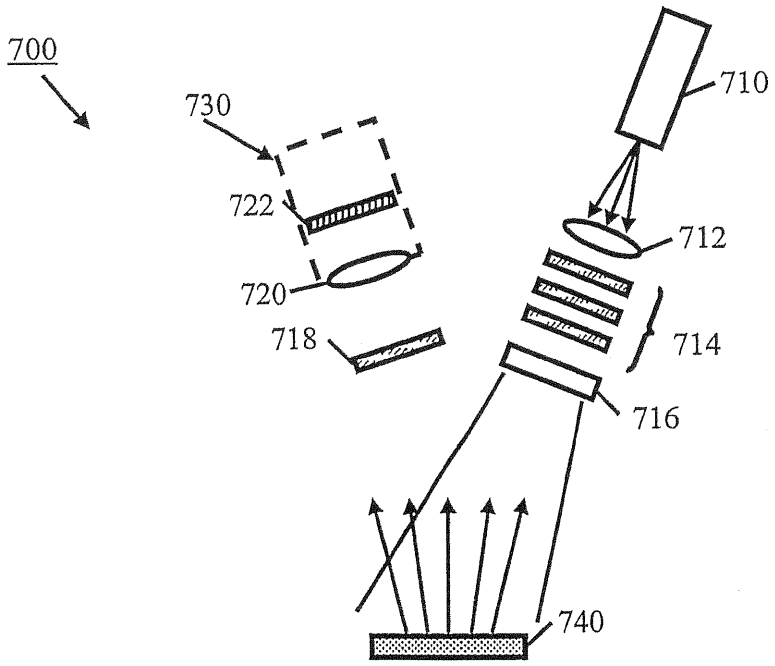


FIG. 7